



## TO-92 Plastic-Encapsulate Transistors

### 2N6717 TRANSISTOR ( NPN )

#### FEATURES

Power dissipation

$$P_{CM}: 1.0 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

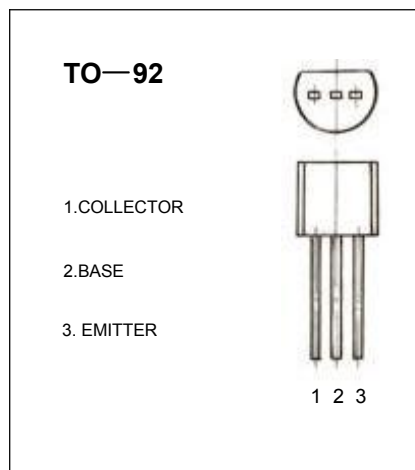
$$I_{CM}: 1.0 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 80 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=0.1\text{mA}, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=1\text{mA}, I_B=0$	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_c=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=80\text{V}, I_E=0$			1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_c=0$			1	$\mu\text{A}$
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_c=50\text{mA}$	50	500		MHz